



P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$ $I_{D}\left(A\right)$				
- 20	$0.00775 \text{ at V}_{GS} = -4.5 \text{ V}$	- 14			
	0.01225 at V _{GS} = - 2.5 V	- 11			

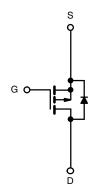
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

Pb-free RoHS COMPLIANT HALOGEN FREE

APPLICATIONS

· Load Switch



P-Channel MOSFET

	SO-8	
S 1 S 2 S 3 G 4		8 D 7 D 6 D 5 D
	Top View	_

Ordering Information: Si4493DY-T1-E3 (Lead (Pb)-free)

Si4493DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise r	noted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 12		V	
Continuous Dunin Courant /T 450 00\8	T _A = 25 °C	- I _D	- 14	- 10		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 11	- 8		
Pulsed Drain Current		I _{DM}	- 50		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.7	- 1.36		
	T _A = 25 °C	D	3.0	1.5	10/	
Maximum Power Dissipation ^a $T_{A} = 70 ^{\circ}\text{C}$ 1.9	0.95	W				
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum boration to Ambienta	t ≤ 10 s	- R _{thJA}	33	42	°C/W	
Maximum Junction-to-Ambient ^a	Steady State		70	84		
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	16	21		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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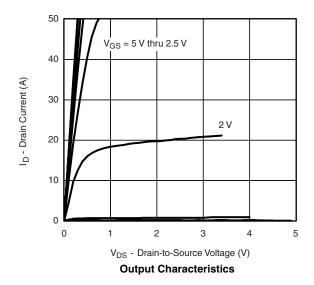
SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min. Typ		Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.6		- 1.4	V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	± 100		± 100	nA		
Zana Oata Vallana Busin Ourmant		V _{DS} = - 20 V, V _{GS} = 0 V	-1		- 1			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 70 °C	T _J = 70 °C - 1			μΑ		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 4.5 V	- 30			Α		
	D	V _{GS} = - 4.5 V, I _D = - 14 A		0.0065	0.00775	Ω		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 11 A		0.010	0.01225	2.2		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 14 A		60		S		
Diode Forward Voltage ^a	V_{SD}	I _S = - 2.7 A, V _{GS} = 0 V		- 0.68	- 1.1	V		
Dynamic ^b								
Total Gate Charge	Q_g			65	110			
Gate-Source Charge	Q _{gs}	Q_{gs} $V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -14 \text{ A}$		14.5		nC		
Gate-Drain Charge	Q_{gd}			21				
Turn-On Delay Time	t _{d(on)}			110	165			
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		150	225	ns		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_g = 6 Ω		220	330			
Fall Time	t _f			140	210			
Gate Resistance	R_g			3.8		Ω		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 2.7 A, dI/dt = 100 A/μs		85	130	ns		

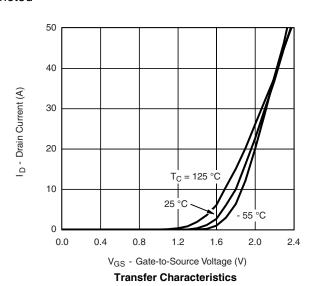
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

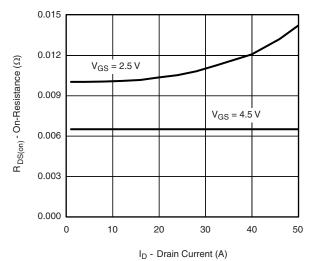




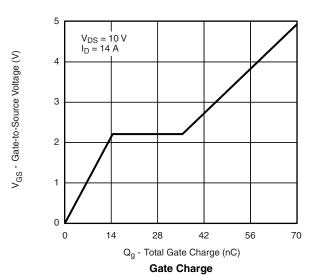


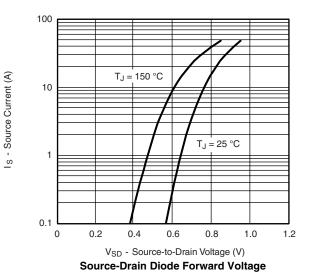


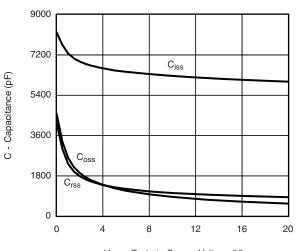
TYPICAL CHARACTERISTICS 25 °C unless noted



On-Resistance vs. Drain Current

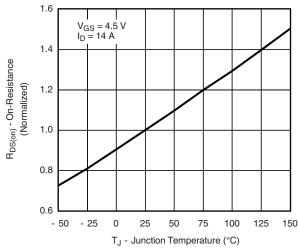




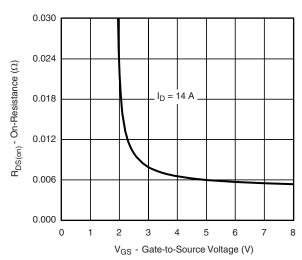


V_{DS} - Drain-to-Source Voltage (V)

Capacitance



On-Resistance vs. Junction Temperature

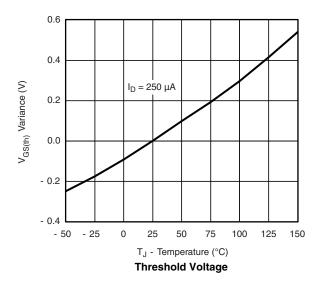


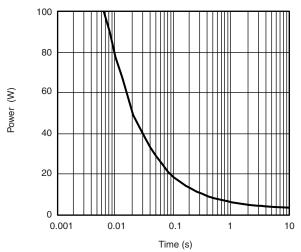
On-Resistance vs. Gate-to-Source Voltage

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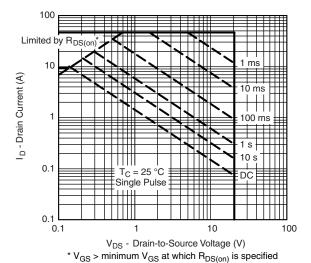
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

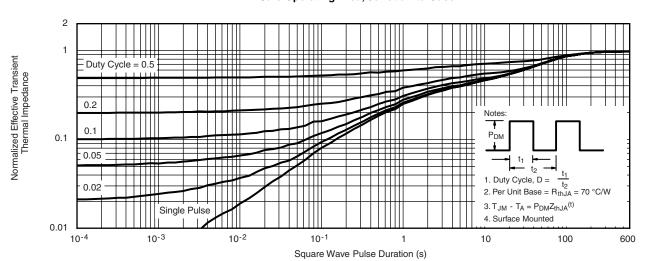




Single Pulse Power, Junction-to-Ambient



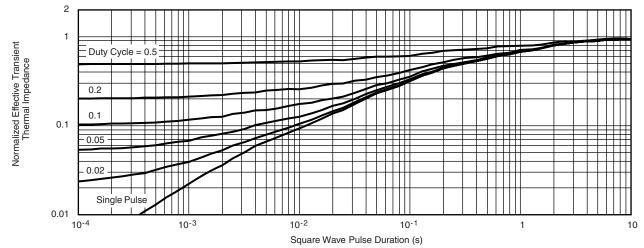
Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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